



SW Test Workshop
Semiconductor Wafer Test Workshop

Verification of Singulated HBM2 stacks with Die Level Handler

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June 4-7, 2017

Background only – will
delete on final material

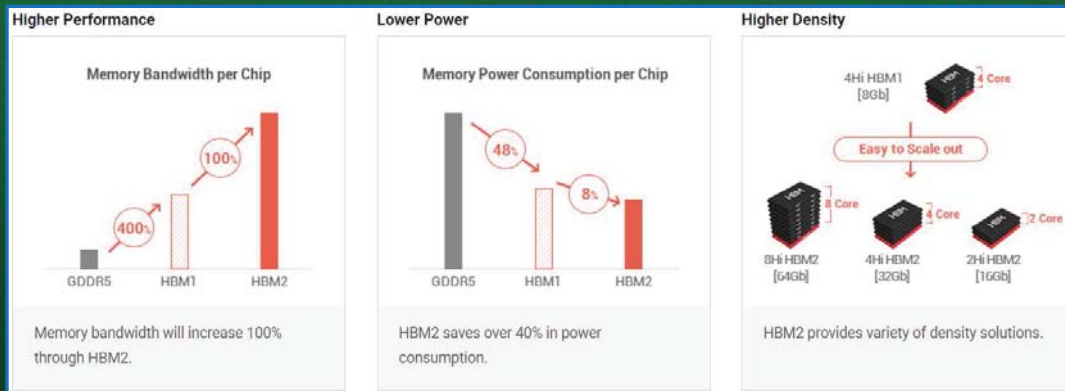
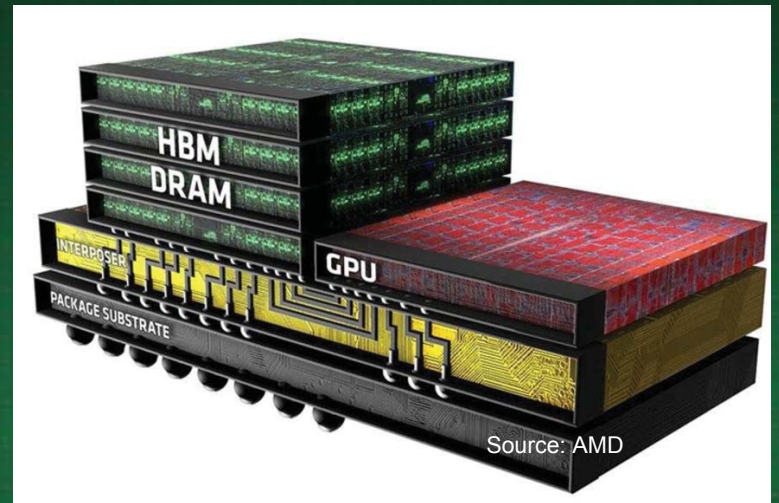
- High-Bandwidth-Memory continues to evolve and demand more stringent testing requirement in terms of test coverage & speed as well as probing accuracy. The recent breakthrough of 2.5D and 3D wafer level packaging technologies has opened up many new possibilities and challenges from test perspectives. A faster tester with higher signal fidelity performance is needed along with an advance probe card technology that can provide the required signal fidelity and the ability to successfully probe on TSV micro-bump structure in an ultra-low pitch grid array. The new test flows and test insertion points needed to validate true “known-good-stack” will be discussed.
- This presentation introduces the HBM2 requirements and addresses the key electrical challenges focusing on simulation versus actual tester measured results collected from direct MicroBump probing above 2 Gbps on all HBM2 Direct Access data channels. Measurement data will be shared from probing HMB2 devices under various probing conditions such as test temperature, test durations, and overdrive, and the various test insertions

Paper Discussion Outline

- **Industry Need for High Performance HBM Memory**
 - HBM process flow and test insertion point
 - Known good stack die probing key challenges
- **Test Cell explanation : T5503HS + HA1000L + FFI Probecard**
- **Probe card design challenges: probing on TSV bump and <60um pitch**
 - Space Transformation, and MEMs spring development
 - Probe card specification
- ⑩ **Direct on Micro-bump probing results**
 - Overdrive versus probe force & probe diameter/depth discussion
 - Ambient scrub mark pictures & result
 - High temperature scrub mark & test result
- **Signal output/input**
 - Simulation vs Actual Measurement result @ 2Gbps
 - 1ch drive vs 8ch simultaneous drive actual result
 - 1.6GHz/3.2Gbps simulation result
- **Proven benefits of this approach & Next Steps**
 - Final product testing
 - High temperature and High frequency
 - Multi-site for future HVM

HBM Addresses the Industry's Need for High Performance Memory

- Increased Bandwidth
- Lower Power Consumption
- Higher Density Package
 - HBM provide higher bandwidth than GDDR5 technology
 - 40% less power consumption
 - Smaller form factor with variety of density solutions

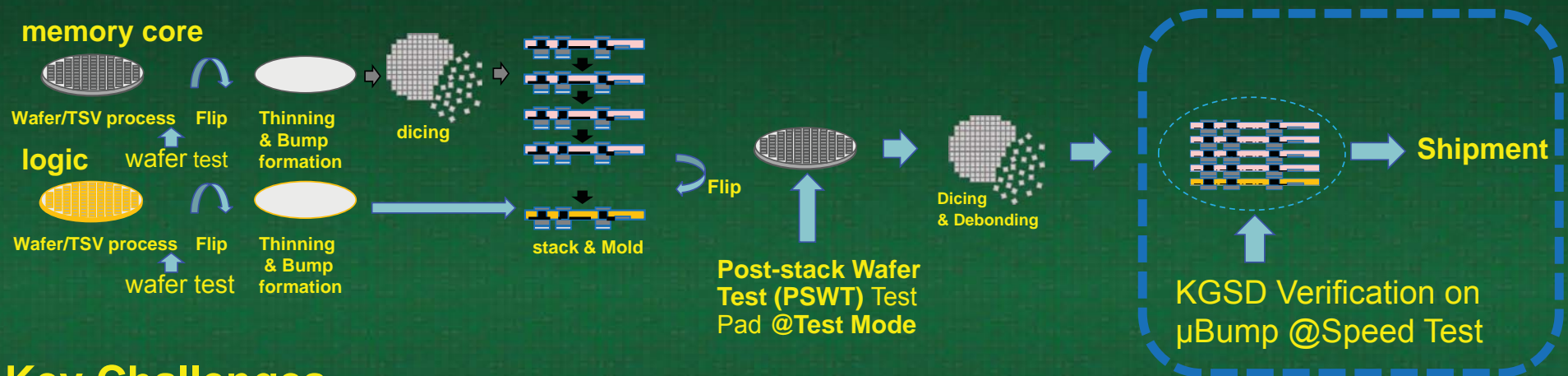


Source: <https://www.skynix.com>

Applications and drivers

- ❖ Graphic card
- ❖ Server/Network
- ❖ Game Console
- ❖ High performance computing
- ❖ Personal Computer
- ❖ Artificial Intelligence

HBM Flow and KGSD Test Challenges



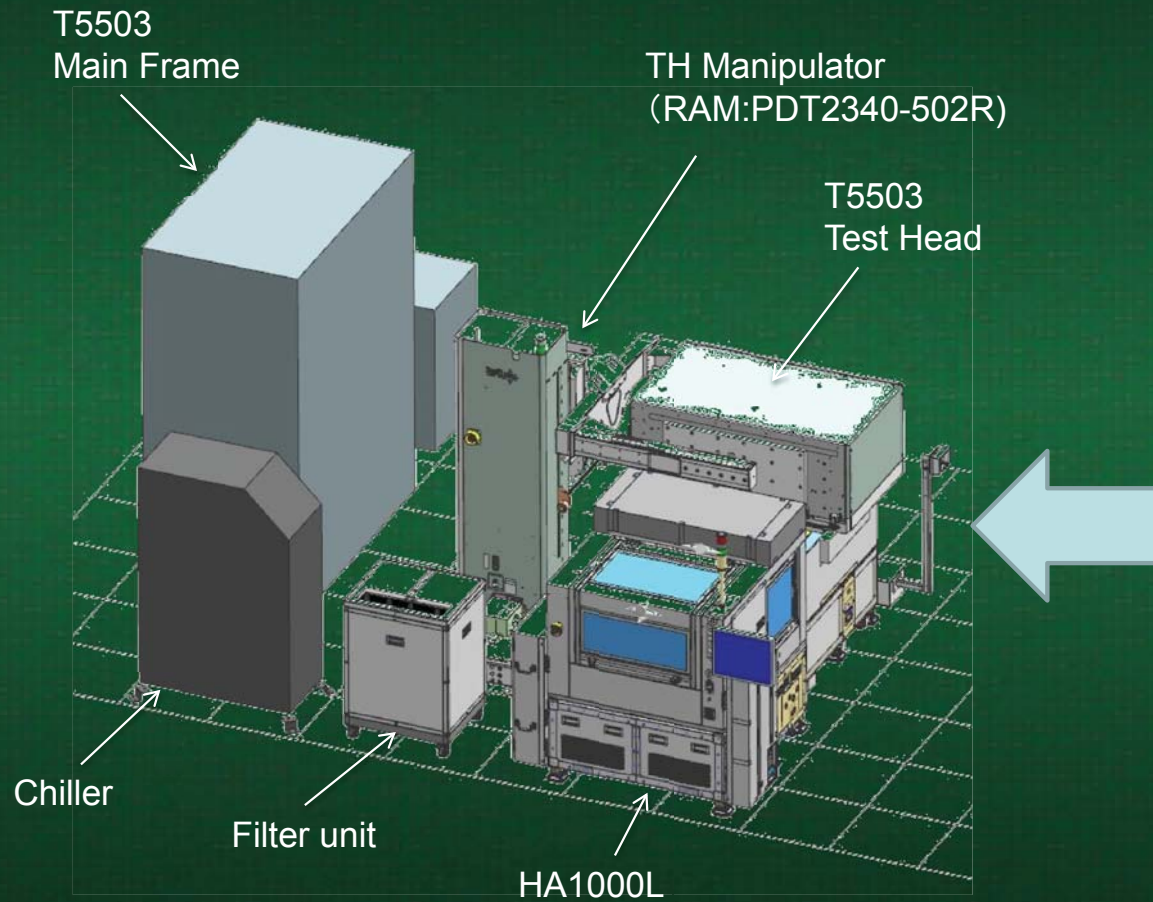
Key Challenges

- Handling of bare stack die
- Thermal movement
- Contact stability at elevated temperature
- Micro-bump “coining” behavior at high temp

Known-Good-Stack Testing Goals

- **Contact all micro-bumps on HBM stacks to allow native mode functional and performance testing on all eight memory channels.**
- **Support at-speed testing > 2.4Gbps.**
- **Confirm hot-temperature and cold-temperature testing.**
- **Reliable contact to >4,000 micro-bumps with a pitch of 55um.**

Test Cell explanation



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Known-Good Stack Probing Solution

HA1000 is a Flexible handling & probing system for singulated die and stack testing.

The HA1000 is ideal for confirming Known Good Die (KGD) and Known Good Stacks (KGS).

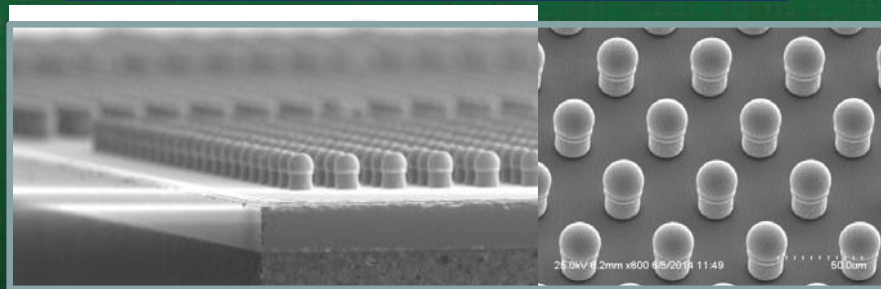
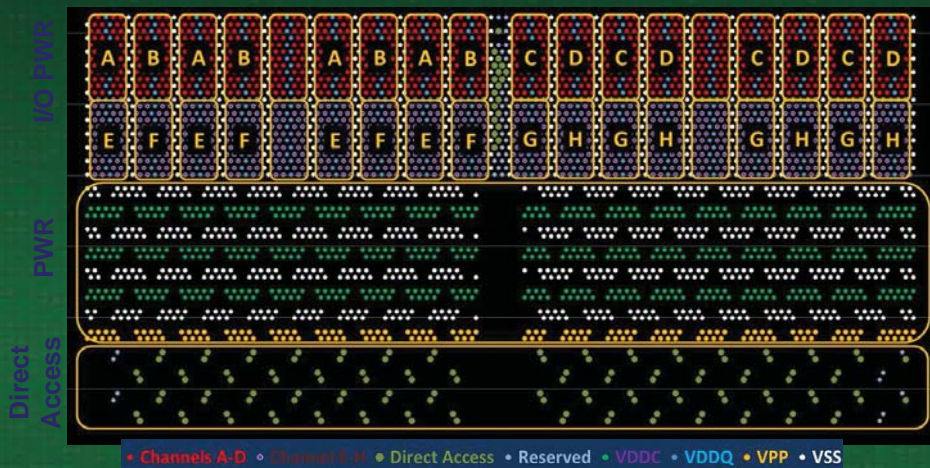


Key Characteristics

- Vision alignment system aligns to the finest geometries.
- Handles 3D stacks regardless of number of die or height.
- Vision alignment aligns to the smallest features.
- Automatic thermal control tests from -40C to +125C.
- Very low thermal resistance.
- Ideal for catching defects before they propagate to the next customer and assembly level.

Probe Card Design Requirement

JEDEC HBM2 Layout Configuration and ST Routing Challenge



■ HBM Array Structure

- Total TSV Micro Bumps: 3990
 - 55μm Micro Bump Pitch (27.5 x 48um staggered)
- Total IO Micro Bumps: 1728
- Direct access micro bumps 176
- Total Power Supplies: 3 – 1056
- Total ground Micro Bumps: 1030

• Array size

- 6022μm x 2832μm

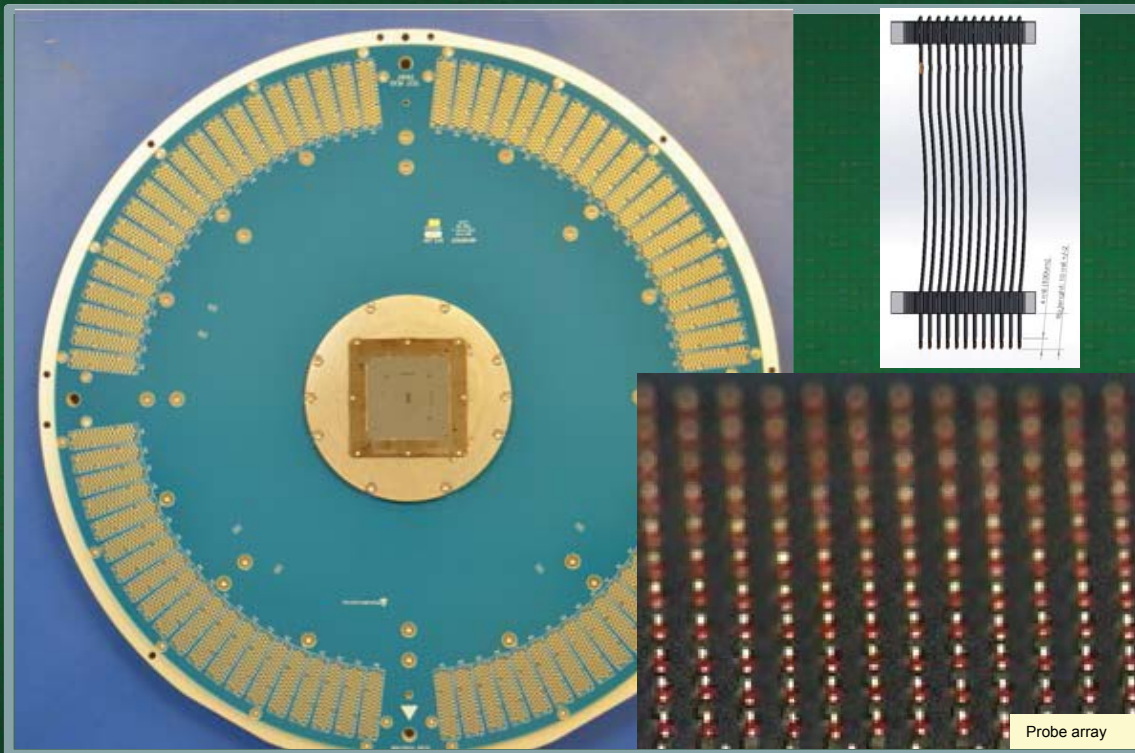
• Test requirement

- 2.133 Gb/s Functional test of the stack
- All 8 device channels

Probe card design challenges

Probing on TSV bump at <math><50\mu\text{m}</math> staggered pitch

Actual FFI Apollo MF40 Probe Card



FormFactor Solution

– Apollo MF40 MEMs

- High speed grid array application
- 1GHz [2Gb/s] on TSV Micro-bump

Challenges:

– Design rules for high speed

- SI simulation validation
- Impedance control from LIF to Tip

– MEMs probe development

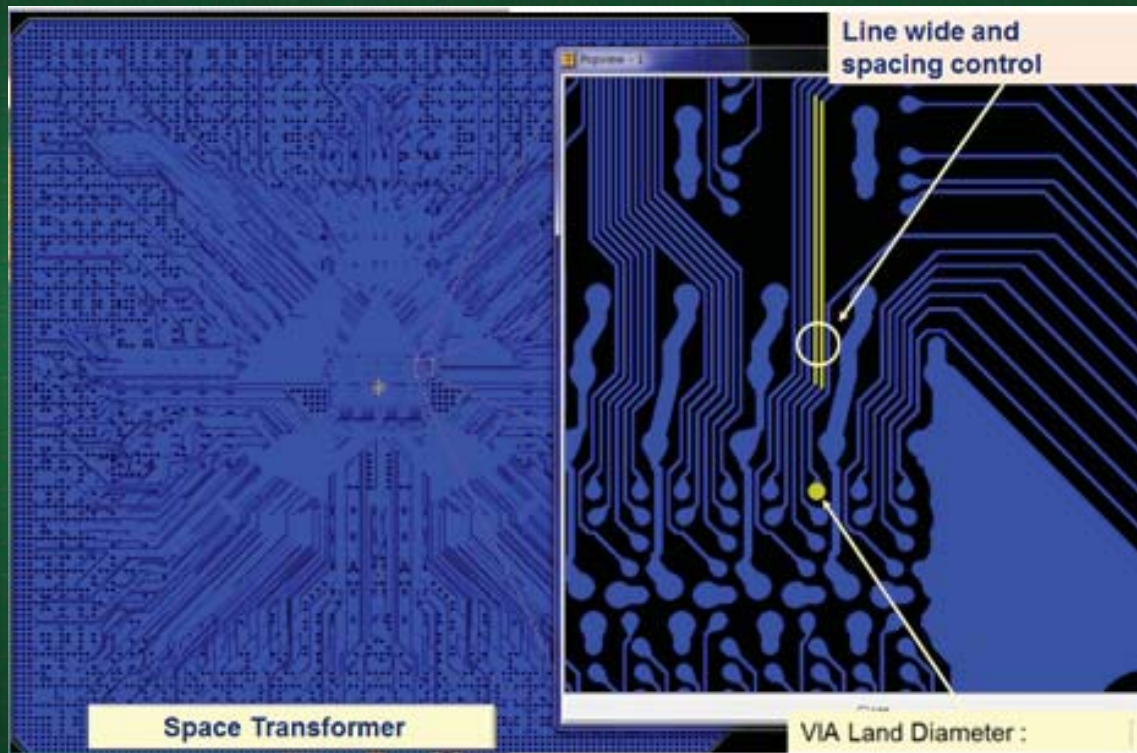
- K-force vs CRES optimization
- Life time vs CCC requirement

– ST Trace geometry

- Line & Space technology
- Routing challenges

– ST Manufacturability

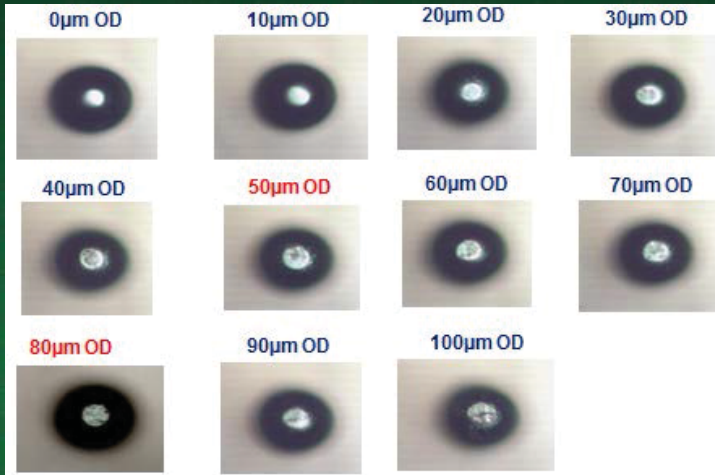
Space Transformation Design Challenges



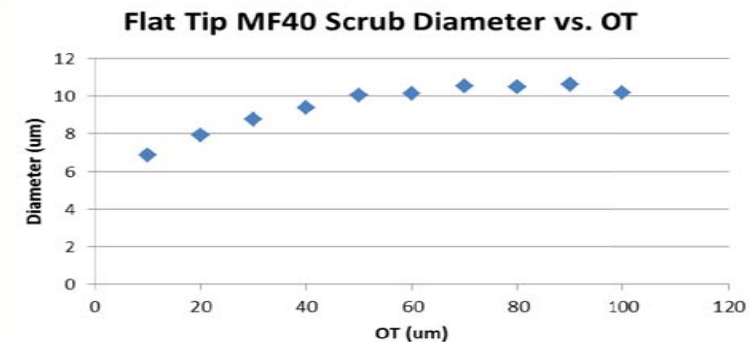
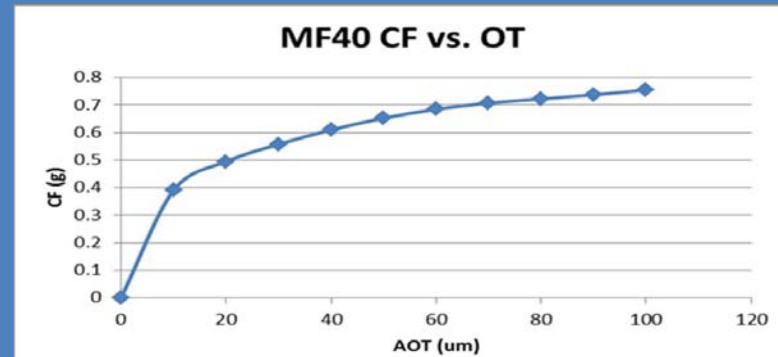
Small die size, high bump counts

- ~4000 traces in ~6x3mm
- FFI proprietary ST MLO fan-out design enabler
- Tight line/spacing requirement and manufacturability
- Impedance control optimization

FFI MF40 Micro-Bump Probing Characteristics

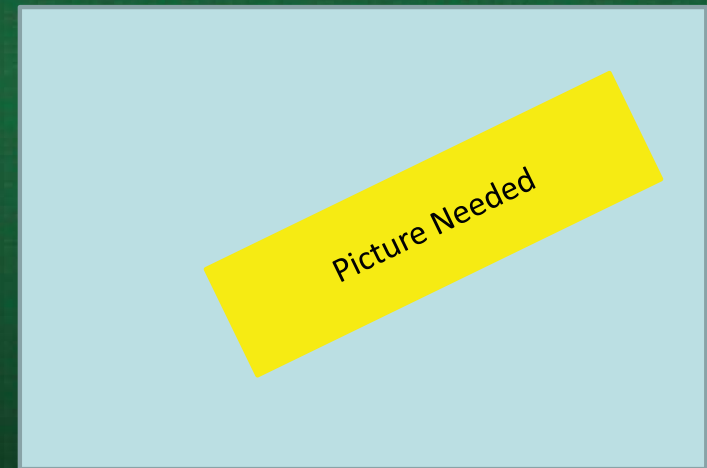
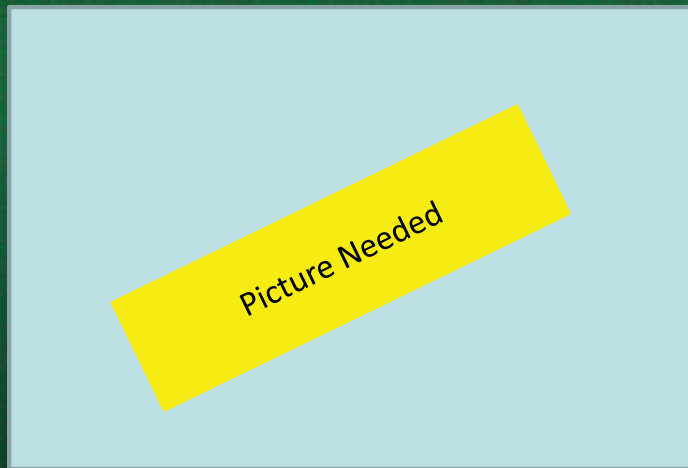


Key Parameter	Specification
Probe technology	FormFactor Vertical MEMS
Tip dimension	22 x 24 µm
Test speed	1 GHz [2Gb/s]
Maximum allowable OT	100µm (50-80µm recommended)
Probe force at recommended OT	0.6-0.8 g
ISMI CCC (Max DC current, 25C)	250mA
Maximum Allowable Current (MAC)	160mA
Tip XY alignment	+/- 12.5µm
Planarity	≤ 25µm



HBM2 Die Micro-bump Probing Results - Ambient

- We succeeded in contacting all I/O pins
- Ambient scrub mark pictures & result
 - Contact Time:6sec, Contact : 1 time vs 2 times
 - Contact Time:60sec, Contact : 1 time vs 2 times

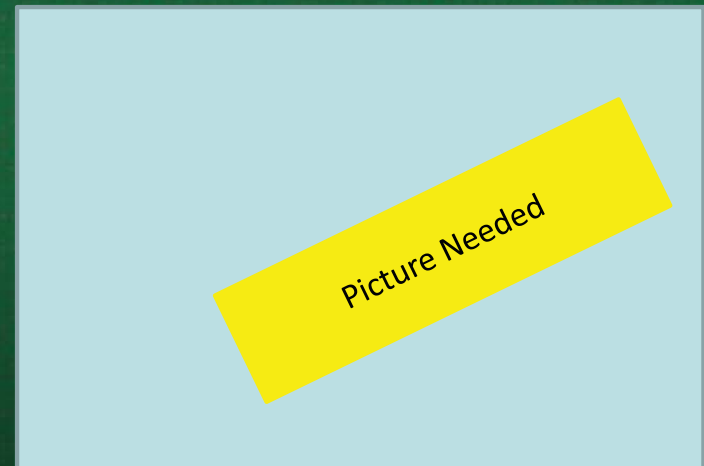


HBM2 Die Micro-bump Probing Results – High Temperature

- We succeeded in contacting all I/O pins
- High temperature scrub mark & test result
 - Contact Time:6sec, Contact : 1 time vs 2 times
 - Contact Time:60sec, Contact : 1 time vs 2 times



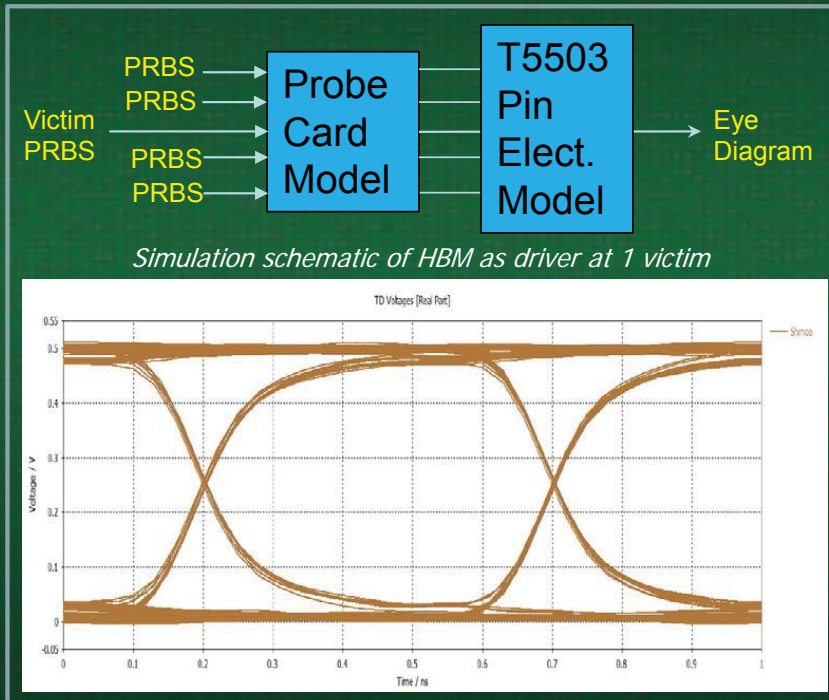
Over Drive:50um



Signal output/input

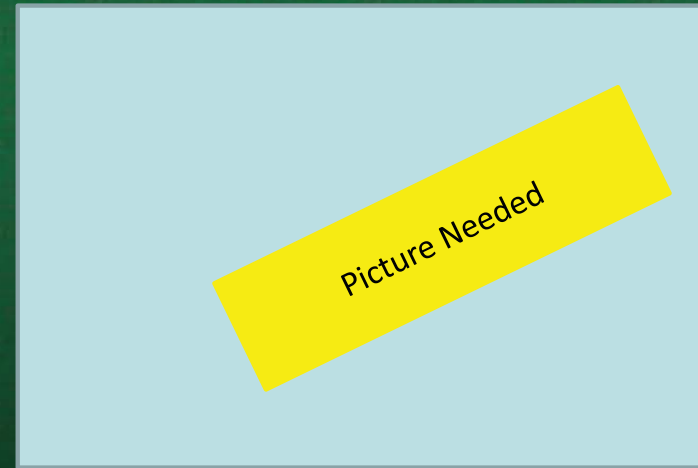
- Simulation vs Actual Measurement result @ 2Gbps

Simulation



Actual Measurement

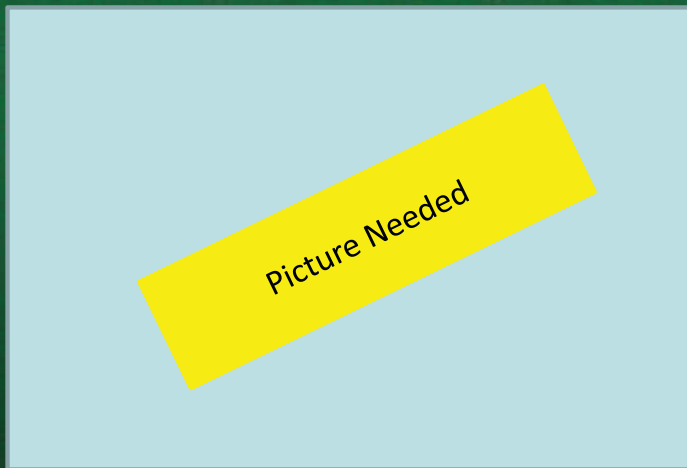
- PRBS signal driver and T5503HS's comparator were terminated with 50Ω.
- Signal height was 1.2V



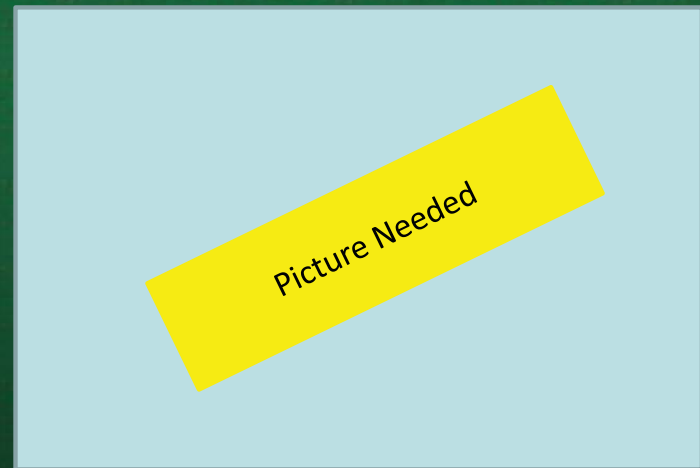
Signal output/input

- **1ch drive vs 8ch simultaneous drive actual result**
 - 1ch measurement / 1ch drive Eye width is bigger than 1ch measurement / 8ch drives

Shmoo(Dout) 1ch meas. / 1ch drive



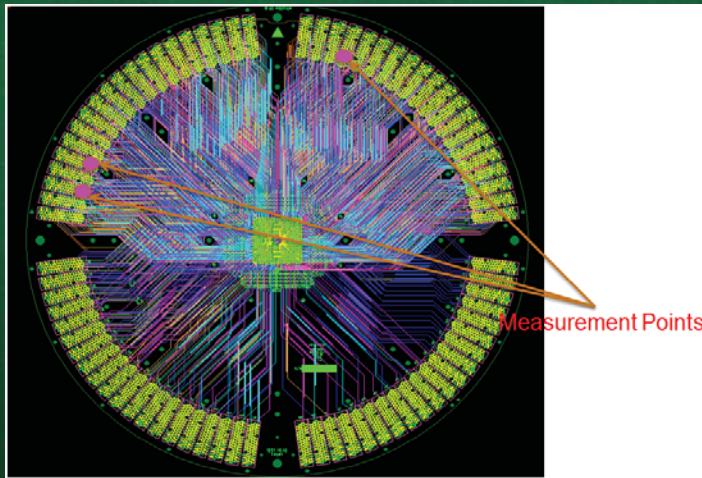
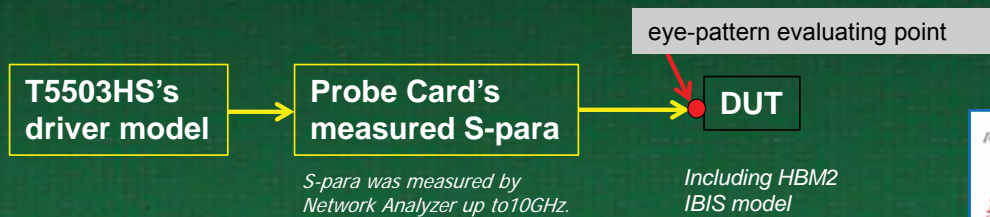
Shmoo(Dout) 1ch meas. / 8ch drives



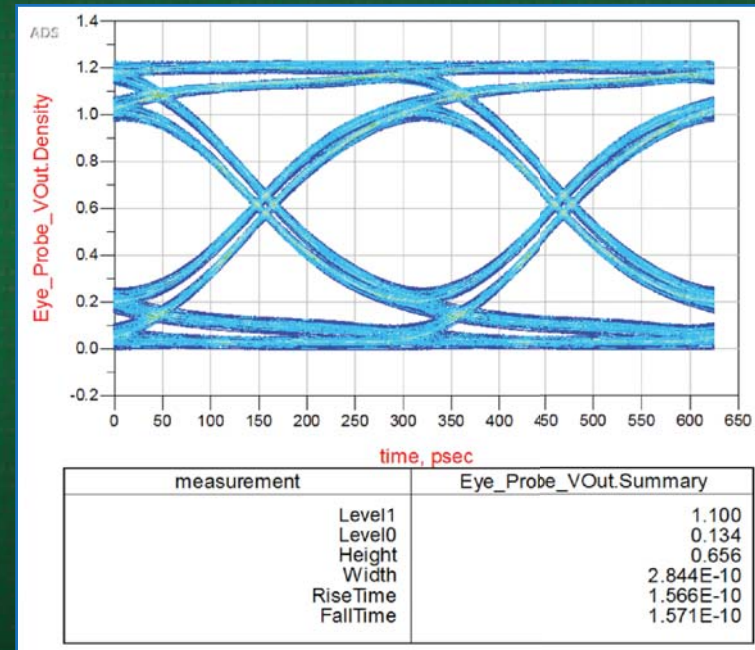
Signal output/input

- 1.6GHz/3.2Gbps simulation result

- MF40 technology supports operating speed to 3.2Gbps with additional design rules optimization



3.2Gbps Signal Performance



Benefit Summary

- Working together as a team Advantest together with FormFactor developed a production worthy tool for confirming Known-Good Memory Stacks with >4,000 micro-bumps and 55um bump pitch.
- The resulting design exceeded our design goals of 0.8g/probe and >160mA CCC with a wide operational temperature range.
- The solution exceeded our high frequency goal demonstrating >3 Gbps performance.
- The solution contacts to all eight HBM channels enabling native mode performance and functional testing of these complex devices.

Contributors

Special thanks to the following contributors to this paper

- Uyen Nguyen
- Todd Swart